

FZT1047A

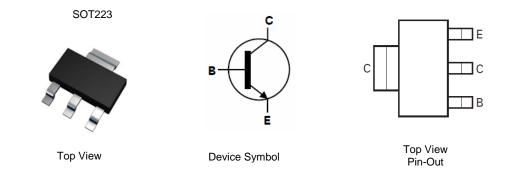
10V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 10V
- I_C = 5A High Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} <45mV @ 500mA
- $R_{SAT} = 44m\Omega @ 5A$ for a Low Equivalent On-Resistance
- h_{FE} Specified up to 20A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.112 grams (Approximate)



Ordering Information (Note 4)

Orderable Part Number	Marking	Reel size (inches)	Topo width (mm)	Packing		
Orderable Part Nulliber	Marking	Reel size (inches)	Tape width (mm)	Quantity	Carrier	
FZT1047ATA	FZT1047A	7	12	1,000	Reel	

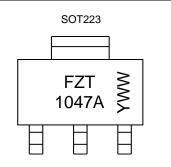
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



FZT 1047A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5 = 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	35	V
Collector-Emitter Voltage	V _{CEO}	10	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	5	A
Peak Pulse Current	I _{CM}	20	A
Base Current	IB	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3		
Power Dissipation	(Note 6)		2	w	
	(Note 7)	P _D	1.6	vv	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)		62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	78.1	°C/W	
	(Note 8)		104	7	
Thermal Resistance Junction to Lead	(Note 9)	R _{θJL}	10.9		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper. Notes:

7. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.

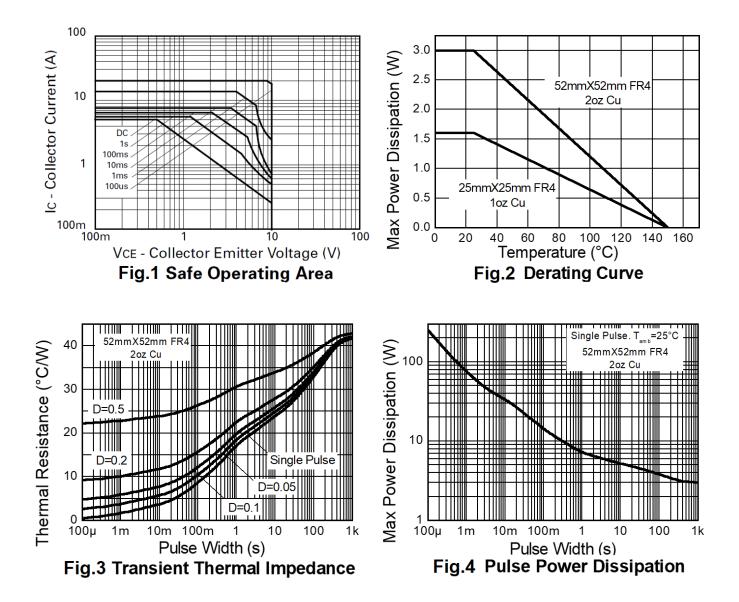
8. Same as note (5), except the device is mounted on minimum recommended pad layout.

9. Thermal resistance from junction to solder-point (at the end of the collector lead).

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





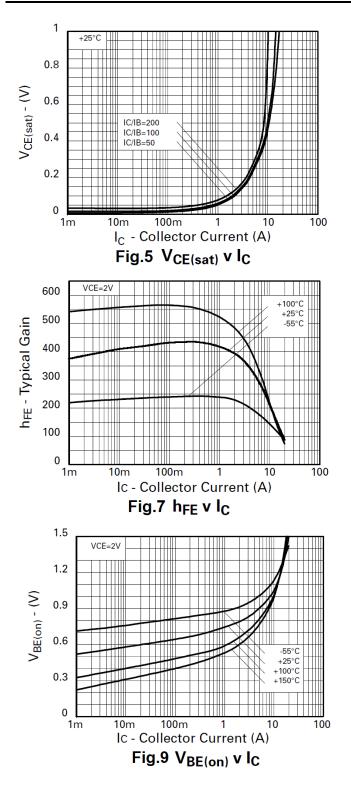
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

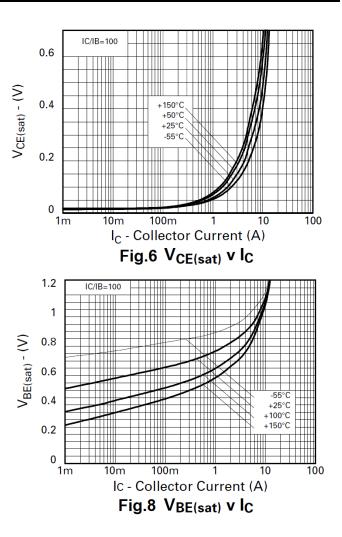
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
	-					
Collector-Base Breakdown Voltage	BV _{CBO}	35	65	—	V	$I_{\rm C} = 100\mu{\rm A}$
Collector-Emitter Breakdown Voltage	BV _{CES}	35	55	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CEV}	35	60	—	V	$I_{C} = 100 \mu A, V_{EB} = 1 V$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	10	16	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BVEBO	7	8.7		V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	_	0.3	10	nA	V _{CB} = 20V
Collector Cut-Off Current	ICES	_	0.3	10	nA	V _{CB} = 20V
Emitter Cut-Off Current	I _{EBO}		0.3	10	nA	$V_{EB} = 4V$
			25	40		$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 10 {\rm mA}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	-	50	70	mV	$I_{C} = 1A, I_{B} = 10mA$
Collector-Emilier Saturation voltage (Note 11)		_	140	200		$I_{\rm C} = 3A, I_{\rm B} = 15mA$
		_	220	350		$I_{\rm C} = 5$ A, $I_{\rm B} = 25$ mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	925	1000	mV	$I_{C} = 5A, I_{B} = 25mA$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	890	975	mV	$I_C = 5A, V_{CE} = 2V$
	h _{FE}	280	430	1200		$I_{C} = 10 mA$, $V_{CE} = 2V$
		290	440			$I_{C} = 0.5A, V_{CE} = 2V$
DC Current Gain (Note 11)		300	450		_	$I_C = 1A, V_{CE} = 2V$
		200	330			$I_C = 5A, V_{CE} = 2V$
		60	110			$I_{C} = 20A, V_{CE} = 2V$
Output Capacitance	C _{obo}		85	110	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	fT	_	150		MHz	$V_{CE} = 10V$, $I_C = 50mA$, f = 50MHz
Switching Times	t _{on}		130	_	20	$I_{C} = 4A, V_{CC} = 10V,$
Switching Times	t _{off}	_	230	—	ns	$I_{B1} = -I_{B2} = 40 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

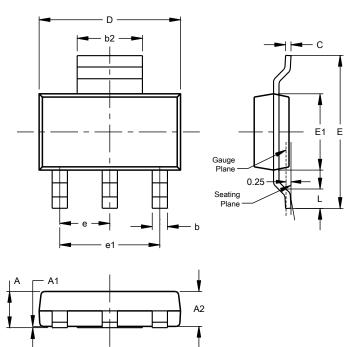






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

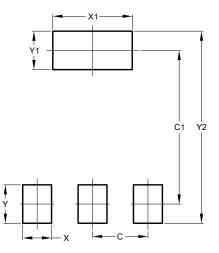


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
e			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

SOT223 (Type DN)



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